



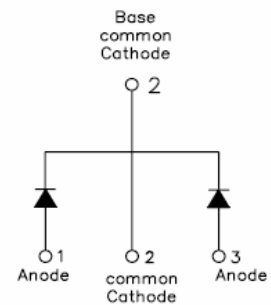
MBR10200CT SCHOTTKY RECTIFIER

Applications:

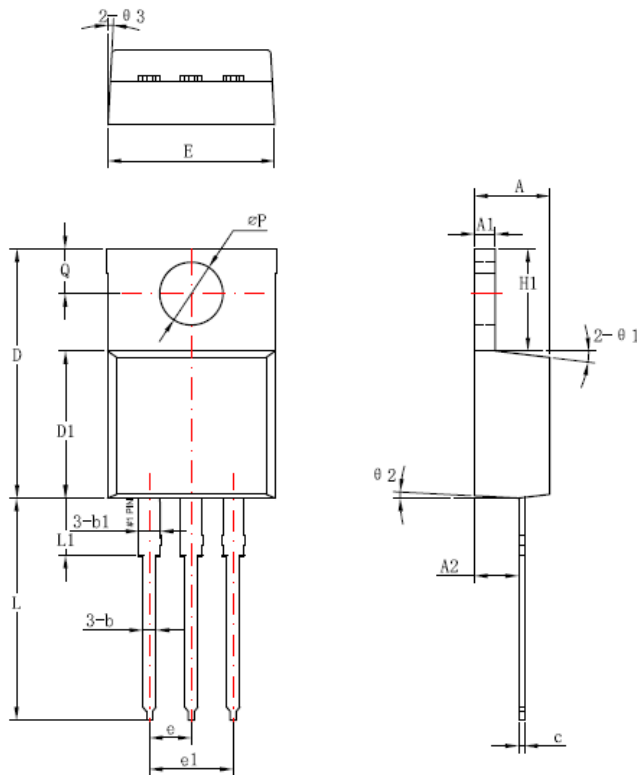
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



Mechanical Dimensions: In mm

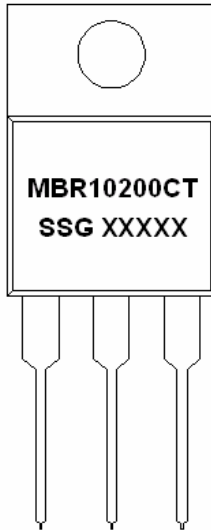


Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	4.42	4.57	4.72
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.35
c	0.36	0.38	0.61
D	14.94	15.24	15.54
D1	8.85	9.00	9.15
E	10.01	10.16	10.31
e		2.54	
e1		5.06	
H1	6.04	6.24	6.44
L	12.7	13.56	13.78
L1		3.5	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
θ1		7°	
θ2		3°	
θ3		4°	

TO-220AB



Marking Diagram:



Where XXXXX is YYWWL

MBR = Device Type
10 = Forward Current (10A)
200 = Reverse Voltage (200V)
CT = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR10200CT	TO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 105^\circ\text{C}$, rectangular wave form	5(Per leg)	A
			10(Per device)	
Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	128	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop (per leg)*	V _{F1}	@ 5 A, Pulse, T _J = 25 °C	0.98	V
	V _{F2}	@ 5 A, Pulse, T _J = 125 °C	0.78	V
Reverse Current (per leg)*	I _{R1}	@ V _R = rated V _R T _J = 25 °C	1	mA
	I _{R2}	@ V _R = rated V _R T _J = 125 °C	7	mA
Junction Capacitance (per leg)	C _T	@ V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	150	pF
Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	8.0	nH
Voltage Rate of Change	dv/dt	-	10,000	V/μs

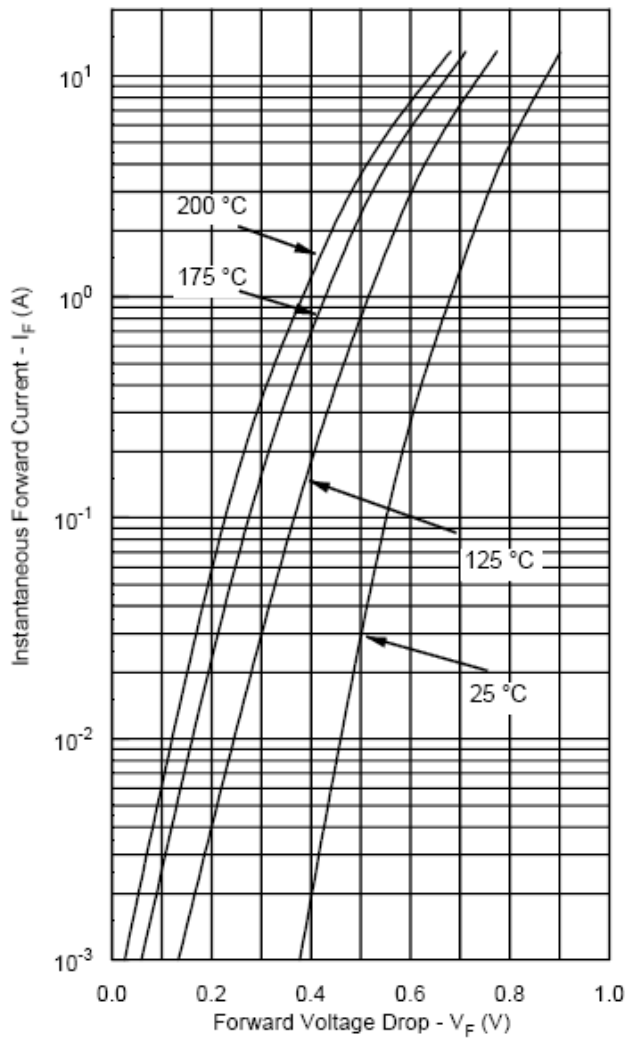
* Pulse Width < 300μs, Duty Cycle <2%

Thermal-Mechanical Specifications:

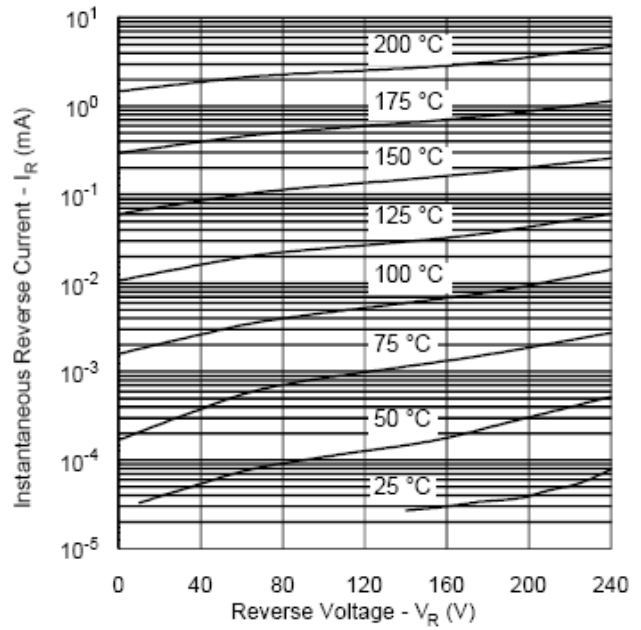
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature Range	T _J	-	-55 to +150	°C
Storage Temperature Range	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case (per leg)	R _{θJC}	DC operation	3.5	°C/W
Maximum Thermal Resistance Junction to Case (per package)	R _{θJC}	DC operation	1.75	°C/W
Maximum Thermal Resistance, Case to Heat Sink	R _{θCS}	Mounting surface, smooth and greased (only for TO-220)	0.50	°C/W
Approximate Weight	wt	-	2	g
Case Style	TO-220AB			



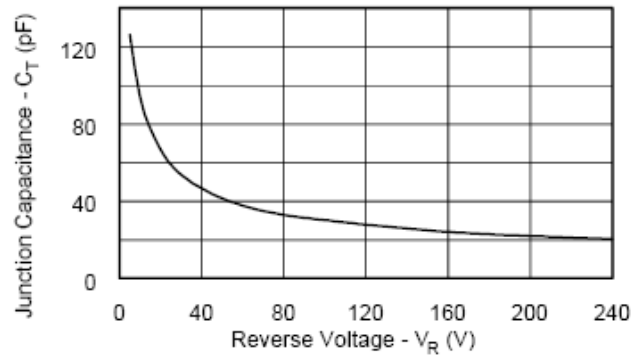
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance





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